

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A manufacturing method of a display device ~~characterized by~~ including a the step of:

forming a wiring by partially forming a conductor film over a substrate by use of plasma treatment means having an electrode for generating plasma at a pressure of 5 to 800 Torr.

2. (Currently Amended) A manufacturing method of a display device ~~characterized by~~ including a the step of:

forming a wiring by partially forming a conductor film over a substrate by use of plasma treatment means having a plurality of electrodes for generating plasma at a pressure of 5 to 800 Torr.

3. (Currently Amended) A manufacturing method of a display device ~~characterized by~~ comprising the steps of:

partially forming a conductor film over a substrate at a pressure of 5 to 800 Torr by use of first plasma treatment means;

forming a resist mask on the conductor film; and

partially etching the conductor film at a pressure of 5 to 800 Torr by use of second plasma treatment means with the resist mask as a mask, and forming a wiring.

4. (Currently Amended) A manufacturing method of a display device ~~characterized by~~ comprising the steps of:

partially forming a conductor film over a substrate at a pressure of 5 to 800 Torr by use of first plasma treatment means having a plurality of electrodes;

forming a resist mask on the conductor film; and

partially etching the conductor film at a pressure of 5 to 800 Torr by use of second plasma treatment means with the resist mask as a mask and forming a wiring.

5. (Currently Amended) A manufacturing method of a display device ~~characterized by~~ comprising the steps of:

partially forming a conductor film over a substrate at a pressure of 5 to 800 Torr by use of first plasma treatment means;

forming a resist mask on the conductor film; and

partially etching the conductor film at a pressure of 5 to 800 Torr by use of second plasma treatment means having a plurality of electrodes with the resist mask as a mask and forming a wiring.

6. (Original) The manufacturing method of the display device according to any of claims 1 to 5, wherein the substrate has a size of 1,000 x 1,200 mm² or more.

7 . (Original) The manufacturing method of the display device according to any of claims 1 to 5, wherein the plasma treatment means scans the substrate in one direction.

8. (Original) The manufacturing method of the display device according to any of claims 1 to 5, wherein the plasma treatment means alternately scans the substrate in a row direction and in a column direction.

9. (Currently Amended) The manufacturing method of the display device according to any of claims ~~1~~ 3 to 5, wherein the resist mask is formed by use of liquid droplet jetting means.

10. (Currently Amended) A manufacturing method of a display device ~~characterized by~~ comprising the steps of:

forming an insulating film covering a thin film transistor; and

partially blowing a reactive gas to the insulating film and forming an open portion.

11. (Currently Amended) A manufacturing method of a display device ~~eharaeterized by~~ comprising the steps of:

forming an insulating film covering a thin film transistor;

forming a resist mask on the insulating film; and

etching the insulating film by using the resist mask as a mask;

wherein the resist mask is formed by photo-lithographically processing a resist film partially formed by liquid droplet jetting means; and

wherein etching of the insulating film includes a step of conducting etching by use of plasma treatment means at a pressure of 5 to 800 Torr.

Please replace the Abstract with the attached separate sheet.